

**REMARKS**

The Lowrey patent relates to a conventional vertical phase change memory. The phase change material is positioned between a heater 130 and an upper electrode.

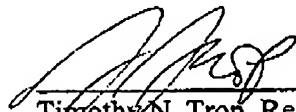
In contrast, the claimed invention here talks about horizontally spaced electrodes and is directed to a lateral phase change memory. It calls for forming a phase change material "between a pair of horizontally spaced electrodes formed on said substantially planar surface." Thus, it is required that the phase change material be formed "between" the horizontally spaced electrodes.

In Lowrey, the phase change material is not formed between the horizontally spaced electrodes, it is formed on top of them so that the electrodes can act as heaters. In contrast, in the claimed lateral phase change memory, the phase change material is between those horizontally spaced electrodes.

Therefore, reconsideration is requested.

Respectfully submitted,

Date: May 4, 2006



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